

CLAIMS TO THE AMENDMENTS

Claims 1-7. (Cancelled)

8. (New) A semiconductor device comprising:

a semiconductor substrate; and

a plurality of trenches, having an interior surface formed by side surfaces and a bottom surface, formed in the semiconductor substrate;

an etching stopper film embedded at least in a selected one of the trenches;

a surface insulating film formed along the side surfaces and bottom surface lining the interior surface of other trenches and along a surface of the semiconductor substrate; and

a conductive film formed at least on the surface insulating film,

wherein the surface insulating film is sufficiently thin to be broken down for forming an electric fuse.